

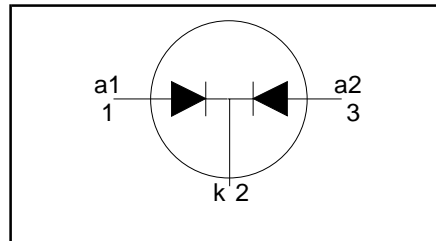
**Dual rectifier diodes  
ultrafast**

**BYT28 series**

**FEATURES**

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Low thermal resistance

**SYMBOL**



**QUICK REFERENCE DATA**

$V_R = 300\text{ V} / 400\text{ V} / 500\text{ V}$
$V_F \leq 1.05\text{ V}$
$I_{O(AV)} = 10\text{ A}$
$t_{rr} \leq 60\text{ ns}$

**GENERAL DESCRIPTION**

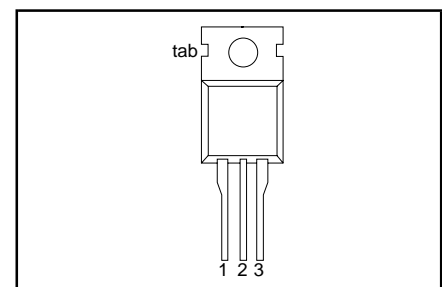
Dual, common cathode, ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYT28 series is supplied in the conventional leaded SOT78 (TO220AB) package.

**PINNING**

PIN	DESCRIPTION
1	cathode
2	anode
tab	cathode

**SOT78 (TO220AB)**



**LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
$V_{RRM}$ $V_R$	Repetitive peak reverse voltage	BYT28 $T_{mb} \leq 147^\circ\text{C}$	-	-300	-400	-500	V
	Continuous reverse voltage		-	300	400	500	V
$I_{O(AV)}$	Average rectified output current (both diodes conducting) <sup>1</sup>	square wave; $\delta = 0.5$ ; $T_{mb} \leq 115^\circ\text{C}$	-	10			A
$I_{FSM}$	Non-repetitive peak forward current per diode.	$t = 10\text{ ms}$	-	50			A
		$t = 8.3\text{ ms}$ sinusoidal; with reapplied $V_{RRM(max)}$	-	55			A
$T_{stg}$	Storage temperature		-40	150			$^\circ\text{C}$
$T_j$	Operating junction temperature		-	150			$^\circ\text{C}$

**THERMAL RESISTANCES**

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Thermal resistance junction to heatsink	per diode	-	-	4.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	both diodes conducting	-	-	3.0	K/W
		in free air.	-	60	-	K/W

<sup>1</sup> Neglecting switching and reverse current losses.

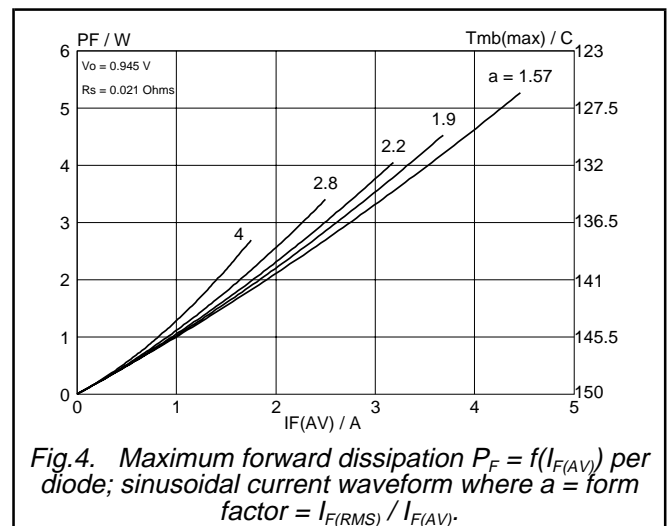
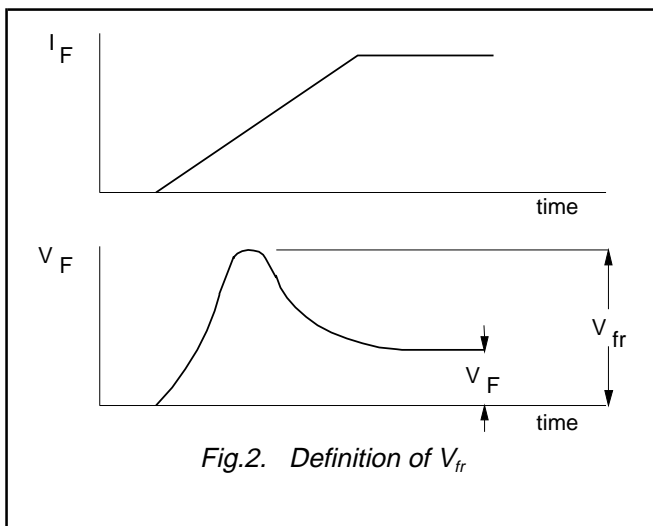
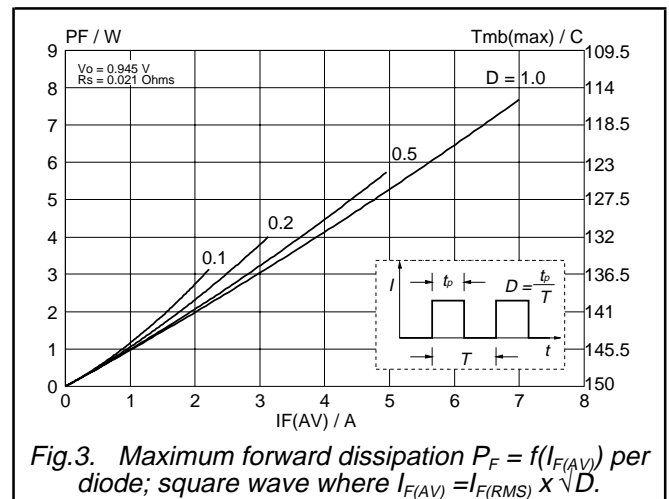
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**ELECTRICAL CHARACTERISTICS**

characteristics are per diode at  $T_j = 25^\circ\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_F$	Forward voltage	$I_F = 5\text{ A}; T_j = 150^\circ\text{C}$	-	0.95	1.05	V
		$I_F = 10\text{ A}$	-	1.30	1.40	V
$I_R$	Reverse current	$V_R = V_{RRM}$	-	2.0	10	$\mu\text{A}$
$Q_s$	Reverse recovery charge	$V_R = V_{RRM}; T_j = 100^\circ\text{C}$ $I_F = 2\text{ A to } V_R \geq 30\text{ V};$ $di_F/dt = 20\text{ A}/\mu\text{s}$	-	10	200	$\mu\text{A}$
$t_{rr}$	Reverse recovery time	$I_F = 2\text{ A to } V_R \geq 30\text{ V};$ $di_F/dt = 100\text{ A}/\mu\text{s}$	-	50	60	ns
$I_{rrm}$	Peak reverse recovery current	$I_F = 5\text{ A to } V_R \geq 30\text{ V};$ $di_F/dt = 50\text{ A}/\mu\text{s}; T_j = 100^\circ\text{C}$	-	2.0	3.0	A
$V_{fr}$	Forward recovery voltage	$I_F = 1\text{ A}; di_F/dt = 10\text{ A}/\mu\text{s}$	-	2.5	-	V



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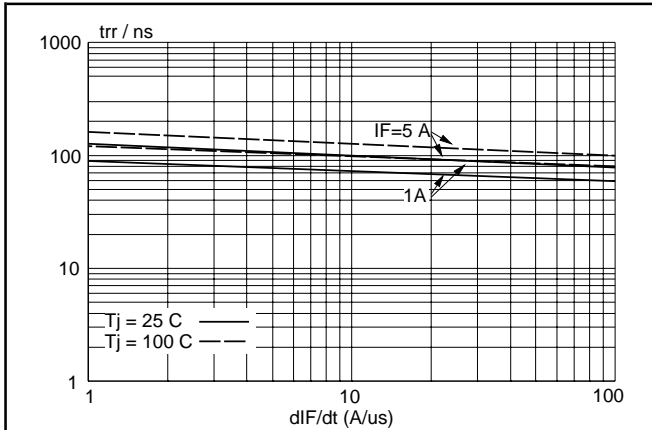


Fig.5. Maximum  $t_{rr}$  at  $T_j = 25^\circ C$  and  $100^\circ C$ ; per diode

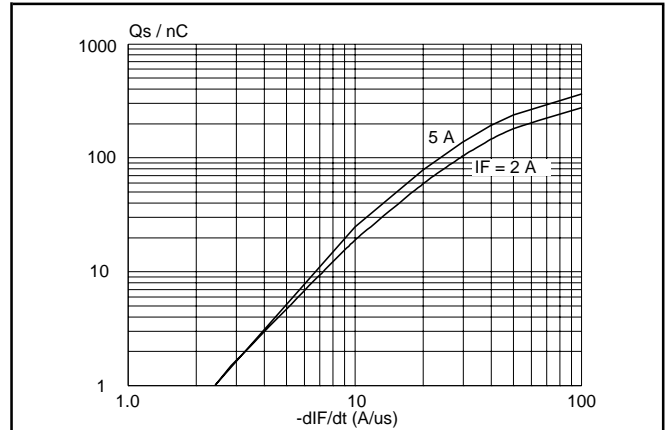


Fig.8. Maximum  $Q_s$  at  $T_j = 25^\circ C$ ; per diode.

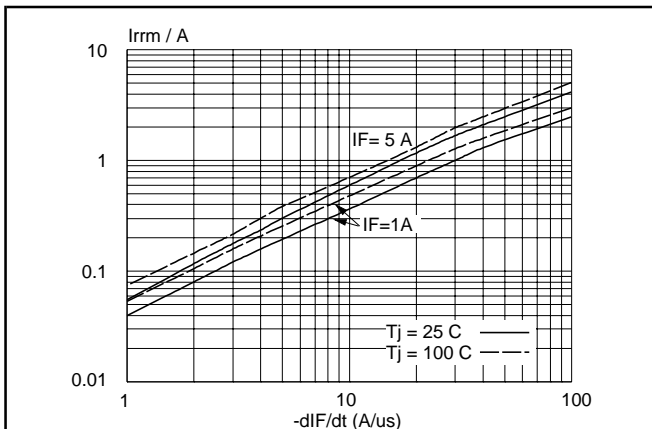


Fig.6. Maximum  $I_{rrm}$  at  $T_j = 25^\circ C$  and  $100^\circ C$ ; per diode.

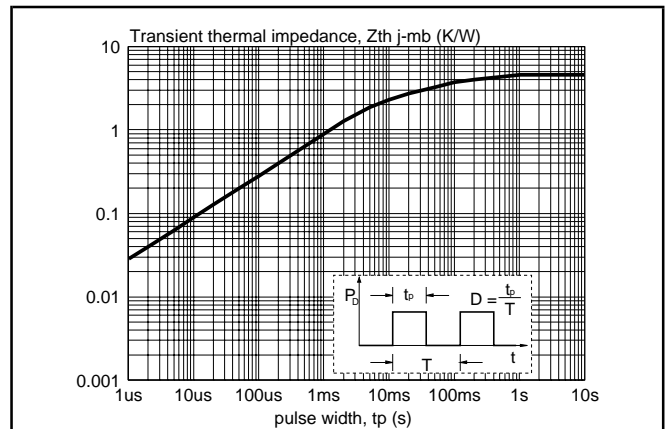


Fig.9. Transient thermal impedance per diode  $Z_{th} = f(t_p)$

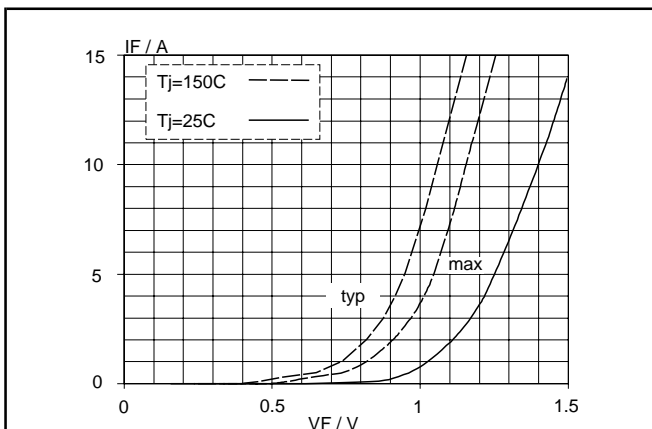
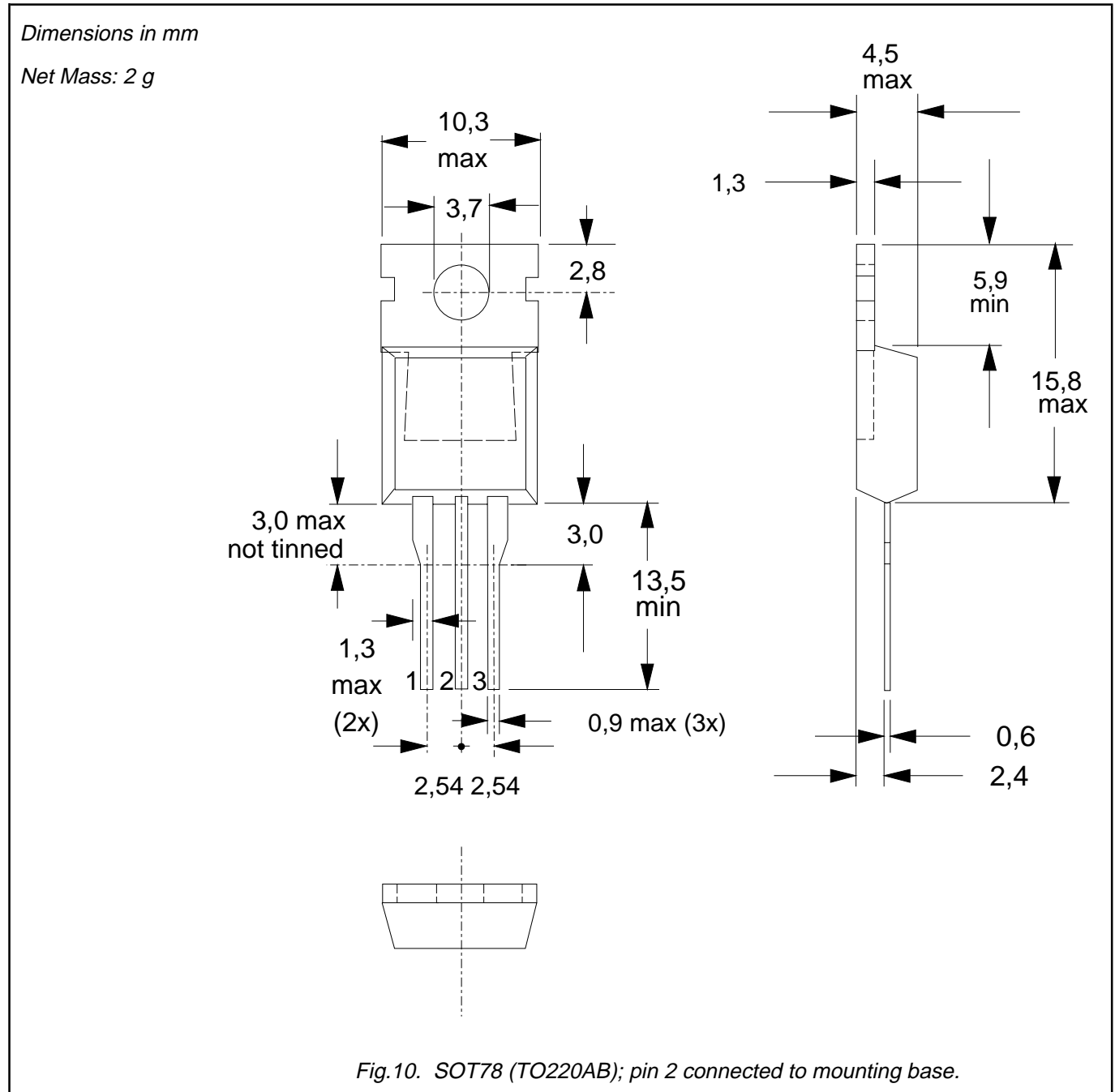


Fig.7. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_j$

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**MECHANICAL DATA**



**Notes**

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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**BYT28 series****DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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